

1 Gigabit Synchronous DRAM

DP5D128ME8XKY5

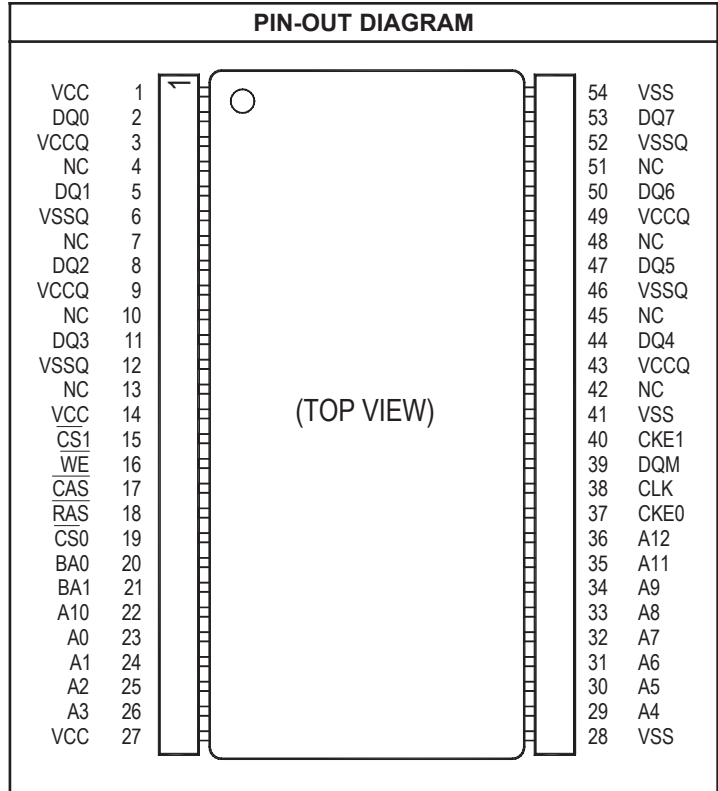
DESCRIPTION:

The Memory Stack™ series is a family of interchangeable memory devices. The 1 Gigabit SDRAM assembly utilizes the space saving LP-Stack™ technology to increase memory density. This stack is constructed with two 512Mb (64M x 8) SDRAMs.

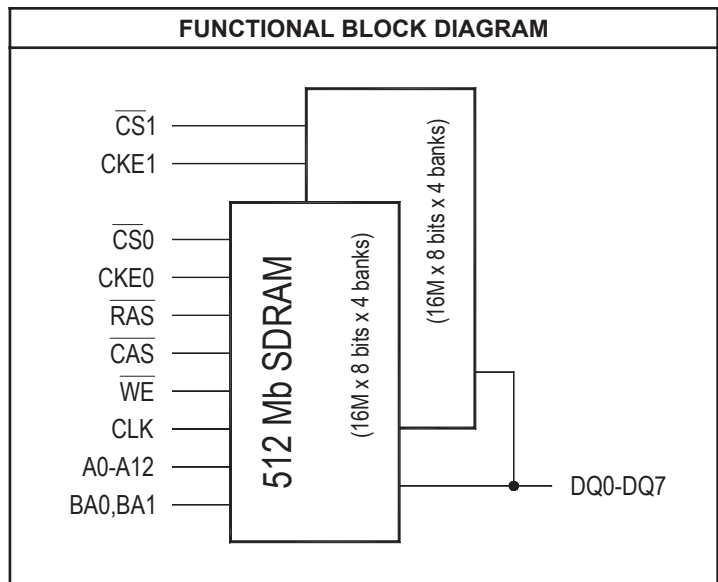
This 1Gb LP-Stack™ has been designed to fit in the same footprint as the 512Mb (64M x 8) SDRAM TSOP11 monolithic. This stack allows for system upgrade without electrical or mechanical redesign, providing an alternative low cost memory solution.

FEATURES:

- Electrical characteristics meet semiconductor manufacturers' datasheets
- Memory organization:
(2) 512Mb Memory devices. Each device arranged as 64M x 8 bits (16M x 8 bits x 4 banks)
- Memory stack organization:
128M x 8 bits (32M x 8 bits x 4 banks)
- JEDEC approved, 2 Rank stack pinout and footprint (with 2 CSs and 2 CKEs)
- Optimized for RDIMMs
- IPC-A-610, class 2, manufacturing standards
- Lead free manufacturing process
- Package: 54-Pin TSOP11 stack



PIN NAMES	
A0-A12	Row Address: A0-A12 Column Address: A0-A9, A11
BA0, BA1	Bank Select Address
DQ0-DQ7	Data In/Data Out
CAS	Column Address Strobe
RAS	Row Address Strobe
WE	Data Write Enable
DQM	Data Input/Output Mask
CKE0, CKE1	Clock Enables
CLK	System Clock
CS0, CS1	Chip Selects
Vcc/Vss	Power Supply/Ground
Vccq/Vssq	Data Output Power/Ground
NC	No Connect



ORDERING INFORMATION

DP	SD	128M	E	8	XK	Y5	- DP -	XX	X	XXX	
PREFIX	TYPE	MEMORY DEPTH	DESIG	MEMORY WIDTH	DESIG	PACKAGE	SUPPLIER	MFR ID	MEMORY REVISION	CYCLE TIME	
											P12 PC100 / CL2
											P13 PC100 / CL3
											12 12ns (83MHz)
											10 10ns (100MHz)
											08 8ns (125MHz)
											75 7.5ns (133MHz) CL3
											75P2 7.5ns (133MHz) CL2
											70 7ns (143MHz) CL3
											70P2 7ns (133MHz) CL2
											60 6ns (166MHz) CL2
											55 5.5ns (183MHz) CL3
											BLANK REVISION NOT SPECIFIED
											n PER MANUFACTURER DIE REVISION
											MANUFACTURER CODE *
											SUPPLIER CODE *
											STACKABLE TSOP
											512 MEGABIT LVTTL BASED
											MODULE WITH DUAL CLOCK ENABLES
											SYNCHRONOUS DRAM

* Contact your sales representative for supplier and manufacturer codes.

NOTE:

1. AC Parameters of base memory are unchanged from device manufacturers' specifications.
2. DC Parameters may be affected by stacking. Please refer to application note 53A004-00 for further information.
3. For assembly and inspection procedures, refer to application note 53A001-00.
4. Maximum reflow temperature recommendation is 215°C.

MECHANICAL DIAGRAM

